

P-Ch MOSFET

General Description

The WSD90P06DN56 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD90P06DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

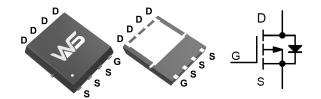
Product Summery

BVDSS	RDSON	ID
-60V	10mΩ	-90A

Applications

- Power Management
- Load Switch

DFN5X6_8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	Drain-Source Voltage -60	
V_{GS}	Gate-Source Voltage	Gate-Source Voltage ±20	
I _D @T _C =25℃	Continuous Drain Current, -V _{GS} @ -10V	-90	Α
I _D @T _C =100°C	Continuous Drain Current, -V _{GS} @ -10V	-40	Α
I _{DM}	Pulsed Drain Current	Drain Current -190	
P _D @T _C =25℃	Total Power Dissipation	96	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$ C
TJ	T _J Operating Junction Temperature Range -55 to 150		$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-Ambient		62	°C/W
R _{0JC}	Thermal Resistance Junction-Case		1.3	°C/W



P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
В	Static Drain-Source On-Resistance	V _{GS} =-10V , I _D =-18A		10	14	m()
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-12A		13	18	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250uA$	-1.1	-1.8	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-48V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, V_{DS} =0V			±100	nA
Qg	Total Gate Charge	Voc. 20 V Voc. 40 V		89		
Q_{gs}	Gate-Source Charge	VDS = -30 V, VGS = -10 V, ID = -17A		12		nC
Q_gd	Gate-Drain Charge			32		
T _{d(on)}	Turn-On Delay Time	VDD = -30 V,		15		
Tr	Rise Time	$RL = 30\Omega$, $ID = -1$ A,		13		no
T _{d(off)}	Turn-Off Delay Time	VGEN = -10 V, $R_g = 6\Omega$		110		ns
T _f	Fall Time			60		
C _{iss}	Input Capacitance	Vps=-30V,Vgs=0V, f=1.0MHz		4066		
Coss	Output Capacitance			501		pF
C _{rss}	Reverse Transfer Capacitance			291		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current	T _C =25 °C			-40	Α
V_{SD}	Diode Forward Voltage	V_{GS} =0 V , I_{S} =-1 A , T_{J} =25 $^{\circ}$ C			-1.2	V

A: The value of Regain measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with Ta=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.

P-Ch MOSFET

P-Channel Typical Characteristics

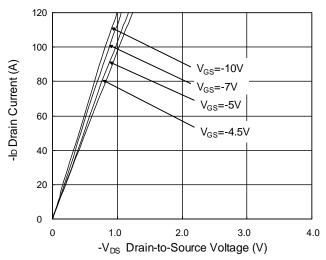


Fig.1 Typical Output Characteristics

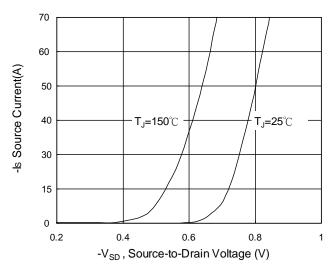


Fig.3 Source Drain Forward Characteristics

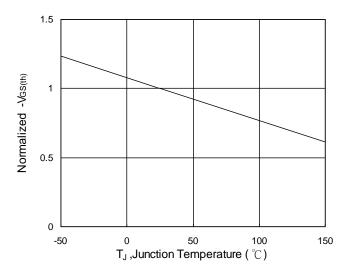


Fig.5 Normalized $V_{GS(th)}$ vs T_J

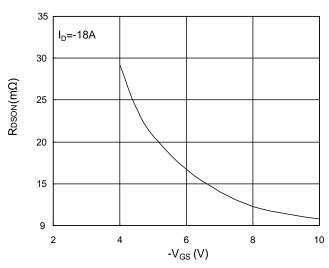


Fig.2 On-Resistance vs G-S Voltage

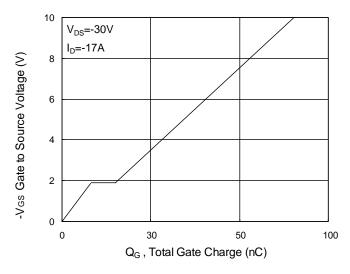


Fig.4 Gate-Charge Characteristics

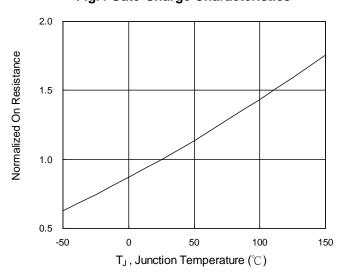


Fig.6 Normalized R_{DSON} vs T_J



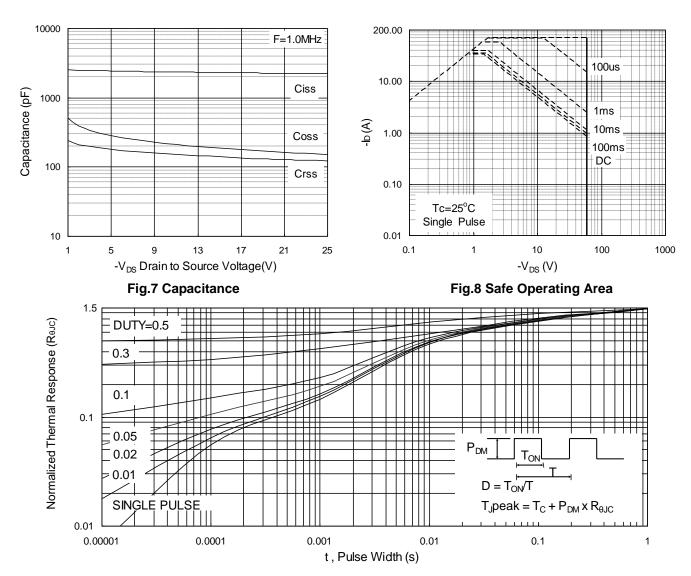


Fig.9 Normalized Maximum Transient Thermal Impedance

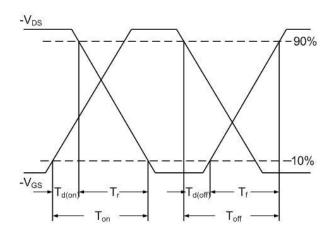


Fig.10 Switching Time Waveform

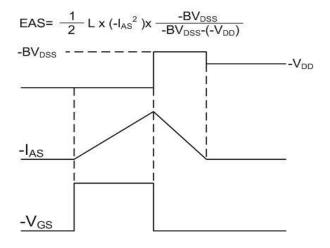


Fig.11 Unclamped Inductive Waveform



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